HS-508BRH



Data Sheet

December 1999 File Number 4824

Radiation Hardened 8 Channel CMOS Analog Multiplexer with Overvoltage Protection

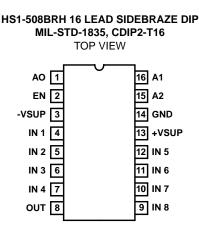
The HS-508BRH is a dielectrically isolated, radiation hardened, CMOS analog multiplexer incorporating an important feature; it withstands analog input voltages much greater than the supplies. This is essential in any system where the analog inputs originate outside the equipment. They can withstand a continuous input up to 10V greater than either supply, which eliminates the possibility of damage when supplies are off, but input signals are present. Equally important, it can withstand brief input transient spikes of several hundred volts; which otherwise would require complex external protection networks. Necessarily, ON resistance is somewhat higher than similar unprotected devices, but very low leakage current combine to produce low errors. Reference Application Notes 520 and 521 for further information on the HS-508BRH multiplexer in general.

The HS-508BRH has been specifically designed to meet exposure to radiation environments. Operation from $-55^{\circ}C$ to $125^{\circ}C$ is guaranteed.

Ordering Information

ORDERING NUMBER	INTERNAL MKT. NUMBER	TEMP. RANGE (^o C)
5962R9674202QEC	HS1-508BRH-8	-55 to 125
5962R9674202QXC	HS9-508BRH-8	-55 to 125
5962R9674202VEC	HS1-508BRH-Q	-55 to 125
5962R9674202VXC	HS9-508BRH-Q	-55 to 125
HS1-508BRH/PROTO	HS1-508BRH/PROTO	-55 to 125
HS9-508BRH/PROTO	HS9-508BRH/PROTO	-55 to 125

Pinouts



Features

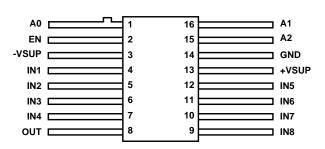
- Electrically Screened to SMD # 5962-96742
- QML Qualified per MIL-PRF-38535 Requirements
- Radiation Environment
 - Gamma Dose (γ) 3 x 10⁵RAD(Si)
 - Dielectrically Isolated Device Islands
 - SEP >100 Mev-mg/cm²
- Analog/Digital Overvoltage Protection
- ESD Rated to 3KV
- Fail Safe with Power Loss (No Latchup)
- · Break-Before-Make Switching
- DTL/TTL and CMOS Compatible
- Analog Signal Range.....±15V
- · Fast Access Time
- Supply Current at 1MHz Address Toggle 4mA (Typ)

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

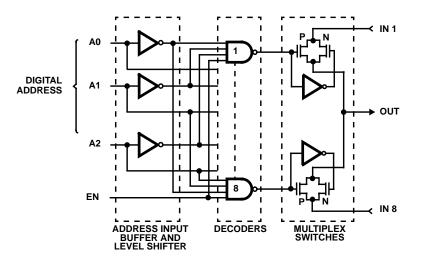
Detailed Electrical Specifications for these devices are contained in SMD 5962-96742. A "hot-link" is provided on our homepage for downloading.

www.intersil.com/spacedefense/newsafclasst.asp

HS9-508BRH 16 LEAD FLATPACK MIL-STD-1835, CDFP4-F16 TOP VIEW



Functional Diagram



A2	A1	A0	EN	"ON" CHANNEL
Х	X	X	L	NONE
L	L	L	Н	1
L	L	Н	Н	2
L	н	L	Н	3
L	н	Н	Н	4
Н	L	L	Н	5
Н	L	Н	Н	6
Н	Н	L	Н	7
Н	Н	Н	Н	8

TRUTH TABLE

Die Characteristics

DIE DIMENSIONS:

120 mils x 93 mils x 19 mils

INTERFACE MATERIALS:

Glassivation:

Type: Phosphorus Silicon Glass (PSG) Thickness: $8k\dot{A} \pm 1k\dot{A}$

Top Metallization:

Type: AlSiCu Thickness: 16kÅ ±2kÅ

Substrate:

Rad Hard Silicon Gate Dielectric Isolation

Metallization Mask Layout

Backside Finish:

Silicon

ASSEMBLY RELATED INFORMATION:

Substrate Potential:

Unbiased (DI)

ADDITIONAL INFORMATION:

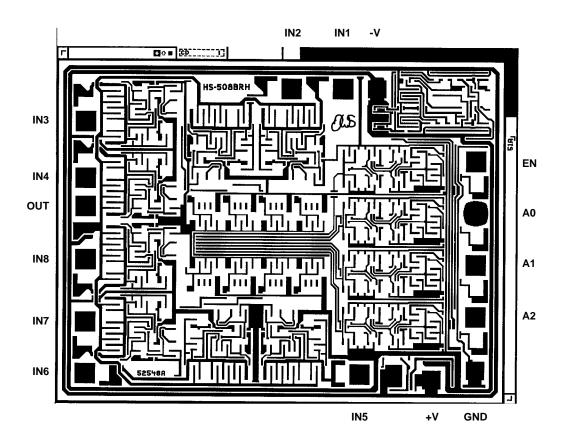
Worst Case Current Density:

6.68e04 A/cm²

Transistor Count:

506

HS-508BRH



All Intersil semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

Intersil semiconductor products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site www.intersil.com

